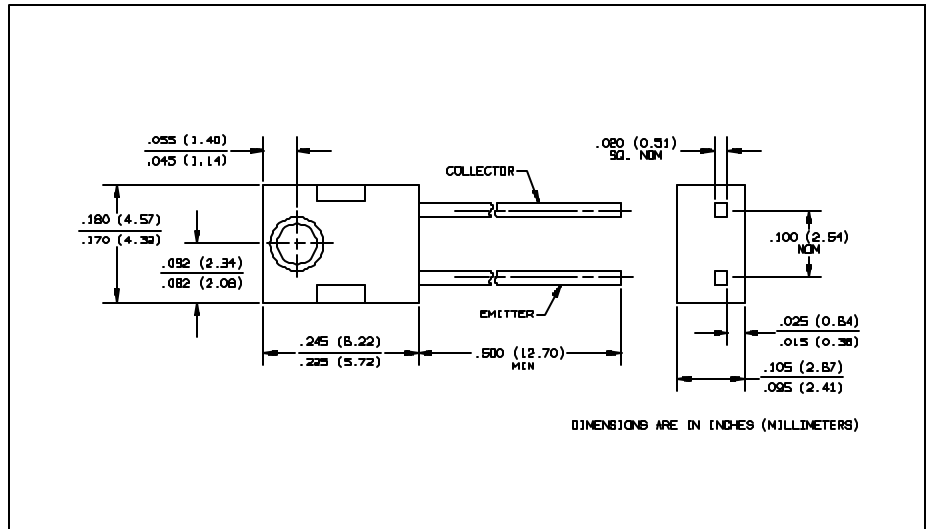


# NPN Phototransistor with Collector-Emitter Capacitor Types OP775A, OP775B, OP775C, OP775D



## Features

- Suppresses high frequency noise
- Variety of sensitivity ranges
- Wide receiving angle
- Side looking package for space limited applications

## Description

The OP775 consists of an NPN phototransistor and 1000 pF capacitor molded in a blue tinted epoxy package. The internal collector-emitter capacitor allows the device to be used in applications where external high frequency emissions could compromise signal integrity.

The device's wide receiving angle provides relatively even reception over a large area.

The OP775 is 100% production tested using an infrared light source for close correlation with Optek's GaAs and GaAlAs emitters.

The side-looking package is designed for easy PC board mounting of slotted optical switches or optical interrupt detectors.

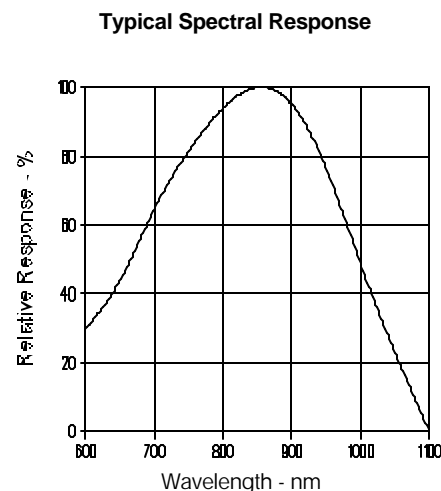
## Absolute Maximum Ratings ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Collector-Emitter Voltage	30 V
Emitter-Collector Voltage	5.0 V
Storage and Temperature Range	$-40^\circ\text{C}$ to $+100^\circ\text{C}$
Lead Soldering Temperature [1/16 inch (1.6 mm) from case for 5 sec. with soldering iron]	$260^\circ\text{C}^{(1)}$
Power Dissipation	$100\text{ mW}^{(2)}$

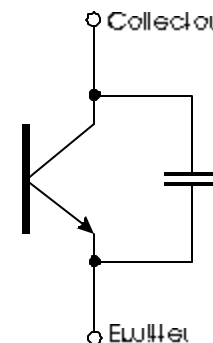
### NOTES:

- (1) RMA flux is recommended. Duration can be extended to 10 sec. max. when flow soldering. Max. 20 grams force may be applied to leads when soldering.
- (2) Derate linearly  $1.33\text{ mW}/^\circ\text{C}$  above  $25^\circ\text{C}$ .
- (3) Light source is an unfiltered GaAs LED with a peak emission wavelength of 935 nm and a radiometric intensity level which varies less than 10% over the entire lens surface of the phototransistor being tested.
- (4) To calculate typical collector dark current in  $\mu\text{A}$ , use the formula  $I_{CED} = 10^{(0.040T_A - 3.4)}$  where  $T_A$  is ambient temperature in  $^\circ\text{C}$ .

## Typical Performance Curves



## Schematic



# Types OP775A, OP775B, OP775C, OP775D

Electrical Characteristics ( $T_A = 25^\circ\text{C}$  unless otherwise noted)

SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS
$I_{C(ON)}$	On-State Collector Current	OP775D	0.70	5.50	mA	$V_{CE} = 5.0\text{ V}, E_e = 1.0\text{ mW/cm}^2(3)$
		OP775C	0.70	2.25		
		OP775B	1.20	3.40		
		OP775A	1.80	5.50		
$\Delta I_C/\Delta T$	Relative $I_C$ Changes with Temperature		100		%/ $^\circ\text{C}$	$V_{CE} = 5.0\text{ V}, E_e = 1.0\text{ mW/cm}^2,$ $\lambda = 935\text{ nm}$
$I_{CEO}$	Collector Dark Current			100	nA	$V_{CE} = 10.0\text{ V}, E_e = 0$
$V_{(BR)ECO}$	Emitter-Collector Breakdown Voltage	5.0			V	$I_E = 100\text{ }\mu\text{A}$
$V_{CE(SAT)}$	Collector-Emitter Saturation Voltage			0.40	V	$I_C = 100\text{ }\mu\text{A}, E_e = 1.0\text{ mW/cm}^2(3)$
$C_{CE}$	Capacitance		1000		pF	$V_R = 0\text{ V}$

## Typical Performance Curves

